TP909FC-900-25 Reverse-conducting Thyristor

2500 V_{DRM}; 1418A rms

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RCT FOR INVERTER AND CHOPPER APPLICATIONS

Features:

- **All Diffused Structure**
- **Interdigitated Amplifying Gate Configuration**
- **Blocking capabilty up to 2500 volts**
- **Guaranteed Maximum Turn-Off Time**
- **High dV/dt Capability**
- **Pressure Assembled Device**

ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V_{DRM} (1)	V_{DSM} (1)
TP909FC-900-20	2000	2000
TP909FC-900-22	2200	2200
TP909FC-900-25	2500	2500

V_{DRM} = Repetitive peak off state voltage

Notes:
All ratings are specified for Tj=25 °C unless otherwise stated.
(1) All voltage ratings are specified for an applied 50Hz/60zHz sinusoidal waveform over the temperature range -40 to +125 °C.
(2) 10 msec. max. pulse width
(3) Maximum value for Tj = 125 °C.
(4) Minimum value for linear and exponential waveshape to 80% rated V_{DRM}. Gate open. Tj = 125 °C.
(5) Non-repetitive value.

Repetitive peak off state leakage	I_{DRM}	20 mA 80mA (3)
Critical rate of voltage rise	dV/dt (4)	1000 V/µsec

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
RMS value of on-state current	I_{TRMS}		1418		A	Nominal value
Average on-state current	$I_{T(AV)}$		903		**A**	Continuous single-phase,half sine wave,180°conduction
Peak one cycle surge (non repetitive) current	I_{TSM}		14000		A	10 msec (60Hz), sinusoidal wave-shape, 180° conduction, T_j = 125 °C
I square t	I^2t		$9.8.x10^5$		A^2s	10.0 msec
Peak on-state voltage	V_{TM}		3.3		V	I_{TM}=3000A
Critical rate of rise of on-state current	di/dt		400		A/µs	V_D=1/2V_{DRM},I_{TM}=800A f=60H_Z I_{GM}=1.5A,di_G/dt=1.0A/us,Tj=125℃
RMS reverse currrnt	$I_{R(RMS)}$		630		A	Nominal value
Average reverse current	$I_{R(AV)}$		400		A	Continuous single-phase,half sine wave,180°conduction
Peak one cycle surge (non repetitive) current	I_{FSM}			6.5	KA	10 msec, sinusoidal wave-shape, T_j = 125 °C
I_R square t	I_R^2t		$1.8.x10^5$		A^2s	10.0 msec
Peak reverse voltage	V_{RM}		2.6		V	I_{RM}=1000A

ELECTRICAL CHARACTERISTICS AND RATINGS (cont.)

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		16		W	t_p = 40 us
Average gate power dissipation	$P_{G(AV)}$		5		W	
Peak gate current	I_{GM}		10		A	
Gate current required to trigger all units	I_{GT}		350		mA	V_D = 6 V;R_L = 2 ohms;T_j = +25 ^oC
Gate voltage required to trigger all units	V_{GT}		2.5		V	V_D = 6 V;R_L = 2 ohms;T_j = 25^oC
Peak non- trigger voltage	V_{GD}		0.2		V	T_j = 125 ^oC;V_D=1/2V_{DRM}

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Turn-off time	t_q	32	40	**40**	µs	I_{TM} =900 A; di_1/dt = -50A/µs; di_2/dt=50A/us,I_{RM}=500A; dV/dt =50 V/µs V_{DR}=2/3 V_{DRM} T_j = 125 ^oC;tw=60us

* For guaranteed max. value, contact factory.

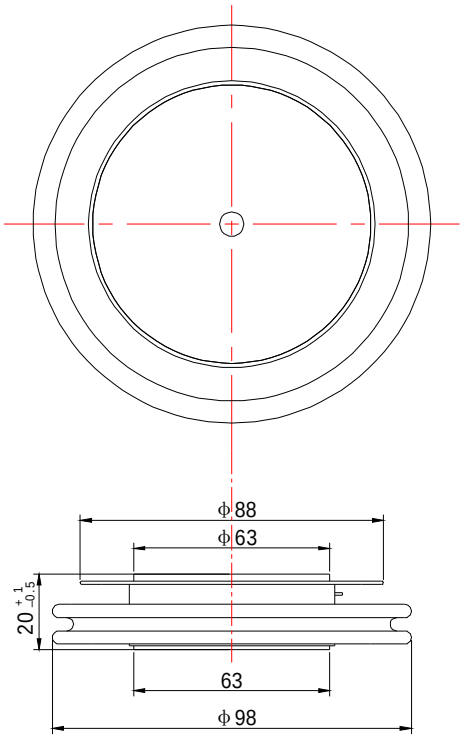
THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+125		^oC	
Storage temperature	T_{stg}	-40	+125		^oC	
Thyristor part thermal resistance - junction to case	$R_{\Theta I\ (j-c)}$		0.022		^oC/W	Double sided cooled
Diode part thermal resistamce – junction to case	$R_{\Theta III\ (j-c)}$		0.050		^oC/W	Double sided cooled
Mounting force	F		30		kN	
Weight	W		700		g	

* Mounting surfaces smooth, flat and greased

Note : for case outline and dimensions, see case outline drawing in page 4 of this Technical Data

CASE OUTLINE AND DIMENSIONS. Reverse-conducting Thyristor



Add:Room303 Weiheng Building No.20 B Area Lanyuan ， Wangyue Rd, Yangzhou Jiangsu P.R.C225000
Contact Person：John Chang, Sam Chou
Tel:+86-514-8736 0558,8778 2298,8778 2296
FAX:+86-514-8778 2297, 8736 7519
SKYPE ID : yzforever0313 MSN ID: john_chang_370@hotmail.com
pst@pst888.com, positioning@china.com,yzforevr@163.net
Marketing web site:
www.pst-thyristor.com
http://positioning.en.alibaba.com/